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EDUCATION

University of Texas at Austin	Ph.D	Electrical and Computer Engineering	2013
University of Texas at Austin	MS	Electrical and Computer Engineering	2009
Seoul National University, Seoul, Korea	BS	Electrical Engineering	2007

PROFESSIONAL ACTIVITIES

- Assistant Professor, Electrical and Computer Engineering Department, UNIST, Republic of Korea, (February 2017 to Present.)
- TCAD Software Engineer, Intel, USA (March 2015 to February 2017)
- Postdoctoral Researcher, SEMATECH, USA (June 2013 to March 2015)

AWARD AND HONORS

- Department Recognition Award, Intel, 2016

MAIN SCIENTIFIC PUBLICATION

- J. E. Seo, D. Seo, **J. Chang***, "Theoretical Analysis on Ballistic Current Transport in Monolayer Black Arsenic MOSFETs", IEEE Transactions on Electron Devices, vol. 67, no. 2, pp. 622-626 (2020).
- J. W. Jeong, Y. E. Choi, W. S. Kim, J. H. Park, S. Kim, S. Shin, K. J. Lee, **J. Chang**, S. J. Kim, and K. R. Kim*, "Tunneling-based ternary metal-oxide-semiconductor technology", Nature Electronics 2, 307–312 (2019).
- D. Seo, **J. Chang***, "Doping-Free Arsenene Heterostructure Metal-Oxide-Semiconductor Field Effect Transistors Enabled by Thickness Modulated Semiconductor to Metal Transition in Arsenene", Scientific Reports 9, 3988 (2019).
- **J. Chang***, "Novel Antimonene Tunneling Field-Effect Transistors Using Abrupt Transition of Semiconductor to Metal in Monolayer and Multilayer Antimonene Heterostructure", Nanoscale 10, 13652-13660 (2018).

RESEARCH INTERESTS

- Nonconventional Material and Device Modeling
- Device Fabrication and Characterization